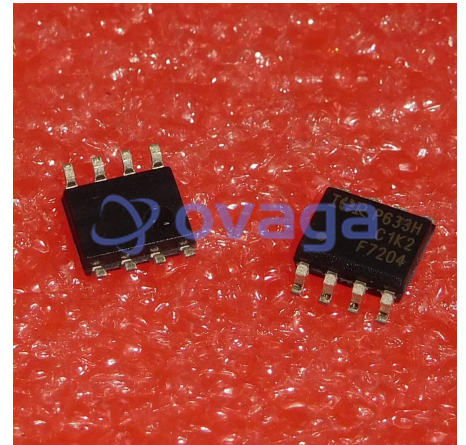


MOSFET, Power, P-Ch; VDSS -20V; RDS(ON) 0.06Ω; ID -5.3A; SO-8; PD 2.5W; VGS +/-12V

Manufacturers	Infineon Technologies Corporation
Package/Case	SO-8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF7204PBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Fourth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

- Advanced Process Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching

Features

RoHS Compliant

Low RDS(on)

Industry-leading quality

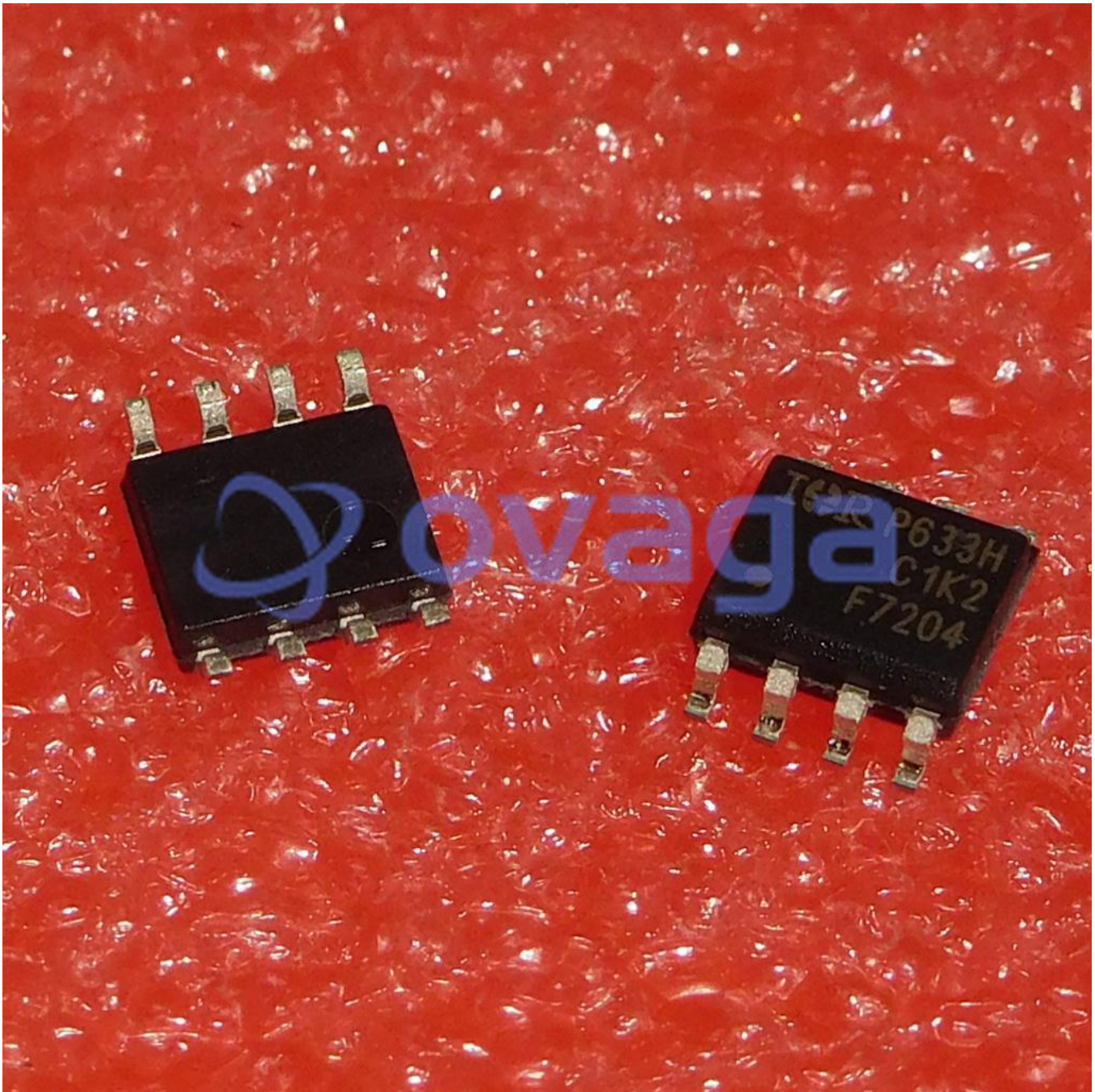
Dynamic dv/dt Rating

Fast Switching

Fully Avalanche Rated

175°C Operating Temperature

P-Channel MOSFET

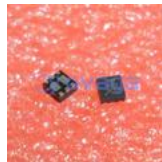


Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

Infineon Technologies Corporation
PQFN2x2DD



[IRF9310PBF](#)

Infineon Technologies Corporation
SOIC-8



[IRFH9310TRPBF](#)

Infineon Technologies Corporation
PQFN-8



[IRF9358TRPBF](#)

Infineon Technologies Corporation
SOP-8



[IRFB7430PBF](#)

Infineon Technologies Corporation
TO-220



[IRFB3307ZPBF](#)

Infineon Technologies Corporation
TO-220AB



[IRF7351TRPBF](#)

Infineon Technologies Corporation
SOIC-8